

Silicon Carbide (SiC) Schottky Diode - EliteSiC, 10 A, 650 V, D2, DPAK

FFSD1065B-F085

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS

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TYPICAL CHARACTERISTICS (CONTINUED)

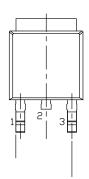
 $(T_J = 25^{\circ}C \text{ UNLESS OTHERWISE NOTED})$

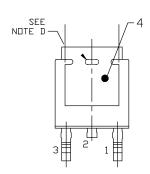
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Figure	7 (Canacitance	Stored	Energy

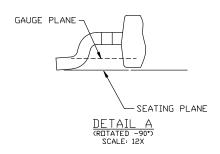


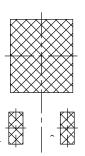
DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS ISSUE B

DATE 20 DEC 2023









LAND PATTERN RECOMMENDATION

GENERIC MARKING DIAGRAM*

XXXXXX XXXXXX AYWWZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code

A = Assembly Location Y = Year

Y = Year WW = Work Week

ZZ = Assembly Lot Code

